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(54) Title: AMPLIFIER AND TRANSCEIVER INCLUDING THE AMPLIFIER

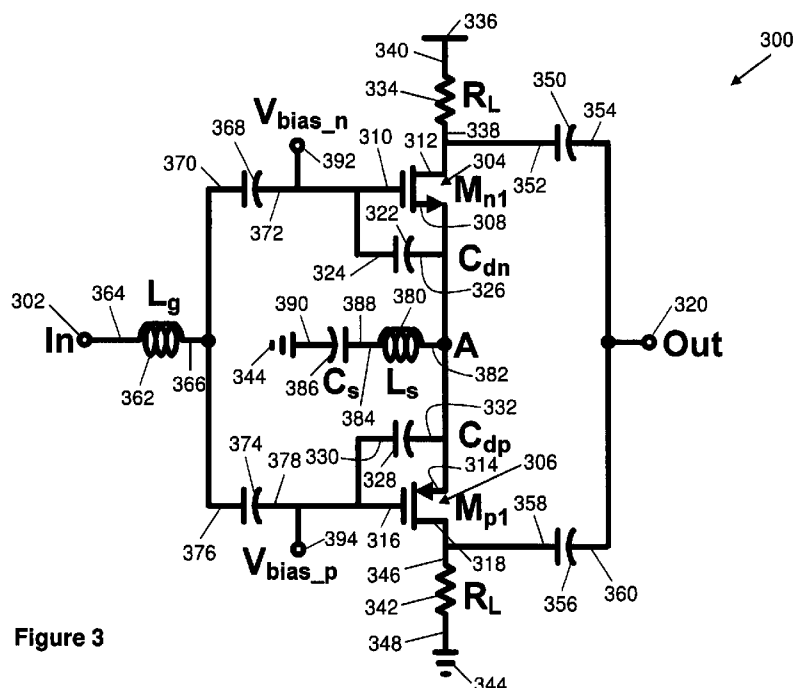


Figure 3

(57) Abstract: An amplifier and a transceiver including the amplifier are provided. The amplifier includes an input terminal; a first transistor of a first conductivity and a second transistor of a second conductivity, each transistor comprising a source terminal, a gate terminal and a drain terminal respectively, the source terminal of the first transistor being coupled to the source terminal of the second transistor, and the gate terminal of the first transistor and the gate terminal of the second transistor being coupled to the input terminal; and an output terminal coupled to the drain terminal of the first transistor and the drain terminal of the second transistor.

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